

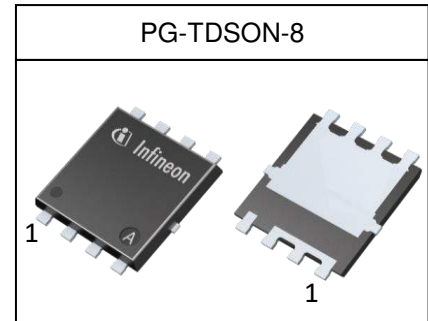
OptiMOS™-5 Power-Transistor

Product Summary

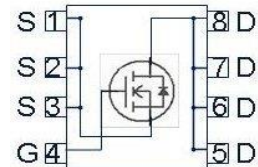
V_{DS}	100	V
$R_{DS(on)}$	30	mΩ
I_D	24	A

Features

- OptiMOS™ - power MOSFET for automotive applications
- N-channel - Enhancement mode - Logic level
- AEC Q101 qualified
- MSL1 up to 260°C peak reflow
- Green product (RoHS compliant)
- 100% Avalanche tested
- Feasible for automatic optical inspection (AOI)



Type	Package	Marking
IAUC24N10S5L300	PG-TDSON-8	5N10L300


Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current ¹⁾	I_D	$T_C=25\text{ °C}, V_{GS}=10\text{V}$	24	A
		$T_C=100\text{ °C}, V_{GS}=10\text{V}$	16	
Pulsed drain current ¹⁾	$I_{D,pulse}$	$T_C=25\text{ °C}$	96	
Avalanche energy, single pulse ¹⁾	E_{AS}	$I_D=10\text{A}$	15	mJ
Avalanche current, single pulse	I_{AS}	-	10	A
Gate source voltage	V_{GS}	-	±20	V
Power dissipation	P_{tot}	$T_C=25\text{ °C}, T_J=175\text{ °C}$	38	W
Operating and storage temperature	T_j, T_{stg}	-	-55 ... +175	°C

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics¹⁾						
Thermal resistance, junction - case	R_{thJC}	-	-	-	3.9	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	6 cm ² cooling area ²⁾	-	-	50	

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=1mA$	100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=12\mu A$	1.2	1.7	2.2	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V, T_j=25\text{ °C}$	-	-	1	μA
		$V_{DS}=100V, V_{GS}=0V, T_j=125\text{ °C}^{1)}$	-	-	20	
Gate-source leakage current	I_{GSS}	$V_{GS}=20V, V_{DS}=0V$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=12A$	-	31	37	m Ω
		$V_{GS}=10V, I_D=12A$	-	23.5	30	
Gate resistance ¹⁾	R_G		-	1.2	-	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics¹⁾

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=50\text{ V}, f=1\text{ MHz}$	-	515	670	pF
Output capacitance	C_{oss}		-	93	121	
Reverse transfer capacitance	C_{rss}		-	7	11	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=50\text{ V}, V_{GS}=10\text{ V}, I_D=24\text{ A}, R_G=3.5\Omega$	-	2	-	ns
Rise time	t_r		-	1	-	
Turn-off delay time	$t_{d(off)}$		-	4	-	
Fall time	t_f		-	3	-	

Gate Charge Characteristics¹⁾

Gate to source charge	Q_{gs}	$V_{DD}=50\text{ V}, I_D=12\text{ A}, V_{GS}=0\text{ to }10\text{ V}$	-	1.7	2.2	nC
Gate to drain charge	Q_{gd}		-	1.6	2.4	
Gate charge total	Q_g		-	7.6	11	
Gate plateau voltage	$V_{plateau}$		-	3.3	-	V

Reverse Diode

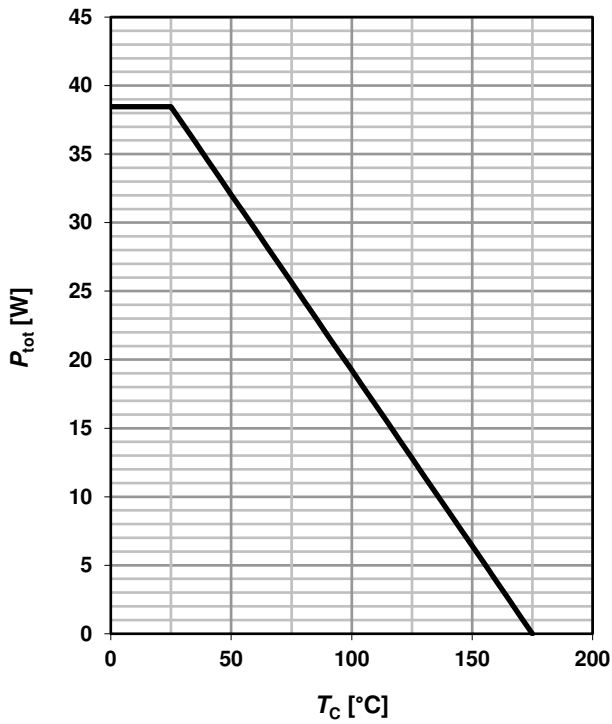
Diode continuous forward current ¹⁾	I_S	$T_C=25^\circ\text{ C}$	-	-	24	A
Diode pulse current ¹⁾	$I_{S,pulse}$		-	-	96	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=12\text{ A}, T_j=25^\circ\text{ C}$	-	0.9	1.1	V
Reverse recovery time ¹⁾	t_{rr}	$V_R=50\text{ V}, I_F=24\text{ A}, di_F/dt=100\text{ A}/\mu\text{ s}$	-	37	-	ns
Reverse recovery charge ¹⁾	Q_{rr}		-	32	-	nC

¹⁾ Defined by design. Not subject to production test.

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

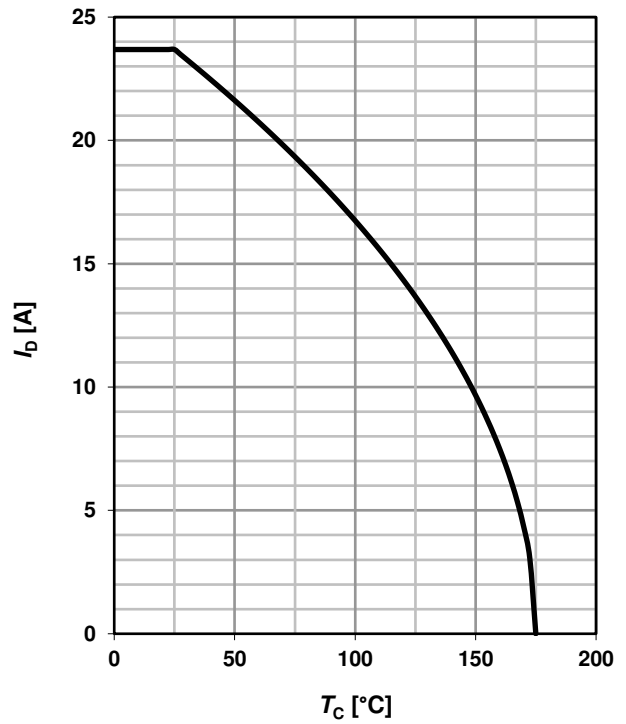
1 Power dissipation

$P_{tot} = f(T_C); V_{GS} \geq 6 V$



2 Drain current

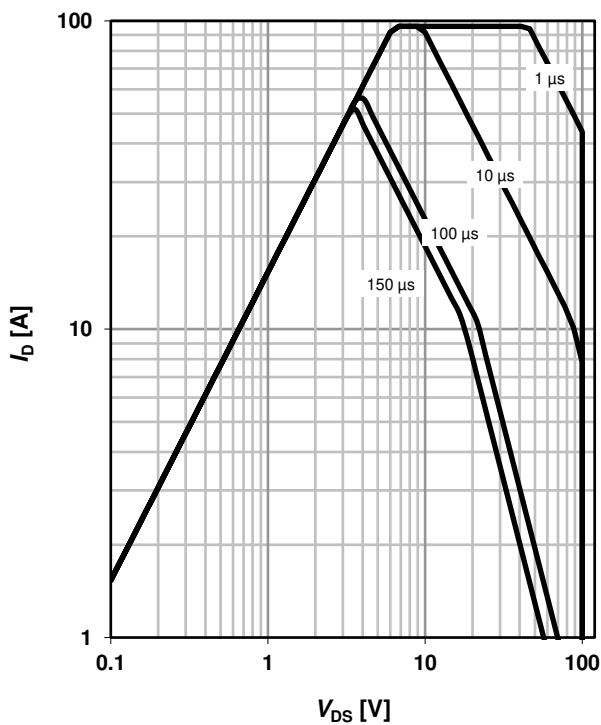
$I_D = f(T_C); V_{GS} \geq 6 V$



3 Safe operating area

$I_D = f(V_{DS}); T_C = 25\text{ °C}; D = 0$

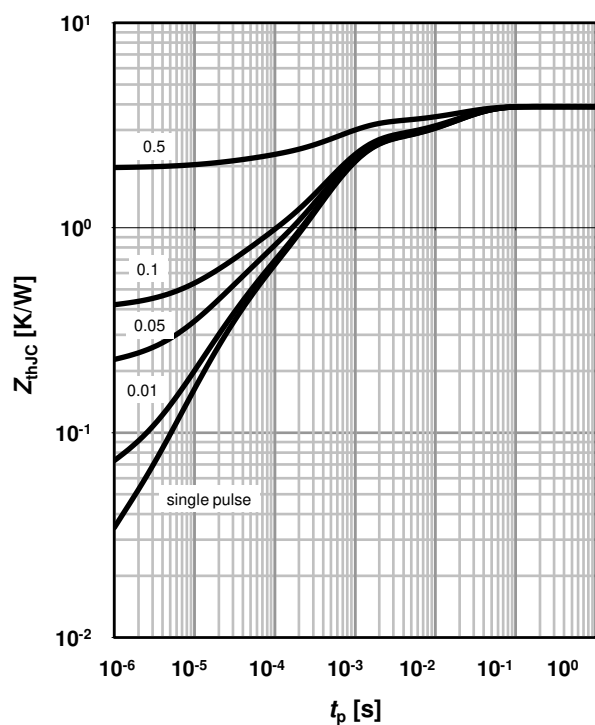
parameter: t_p



4 Max. transient thermal impedance

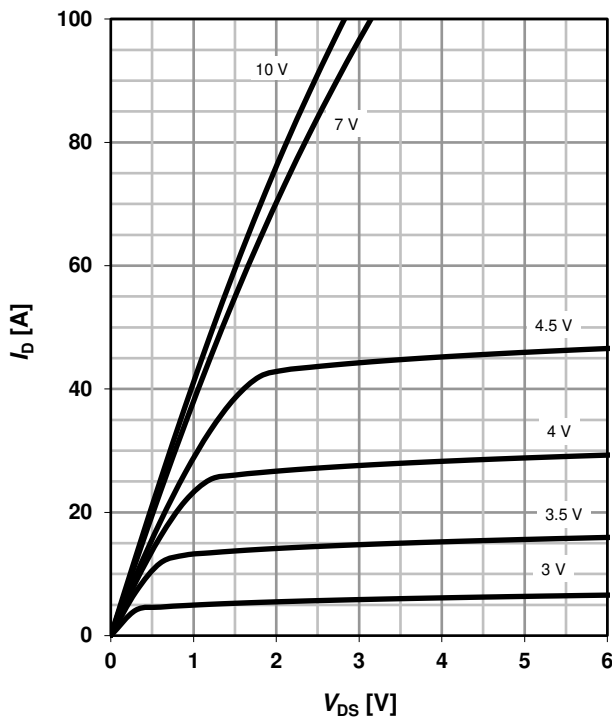
$Z_{thJC} = f(t_p)$

parameter: $D = t_p/T$

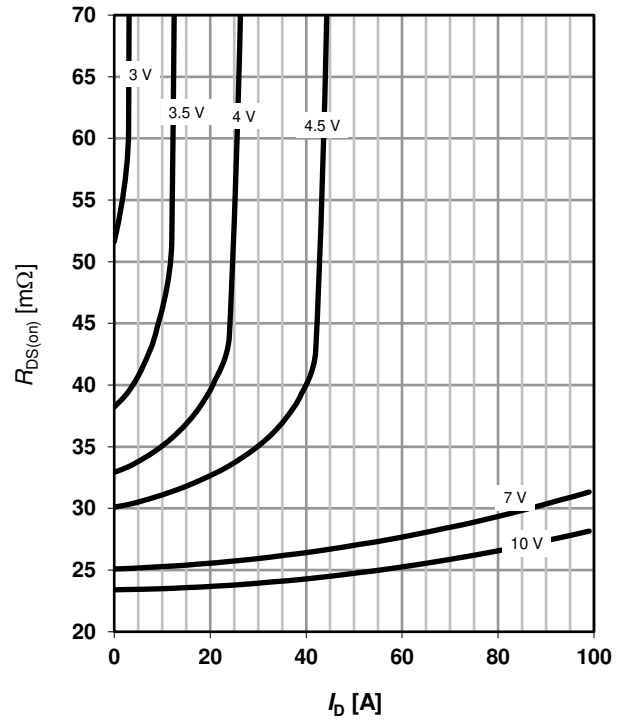


5 Typ. output characteristics

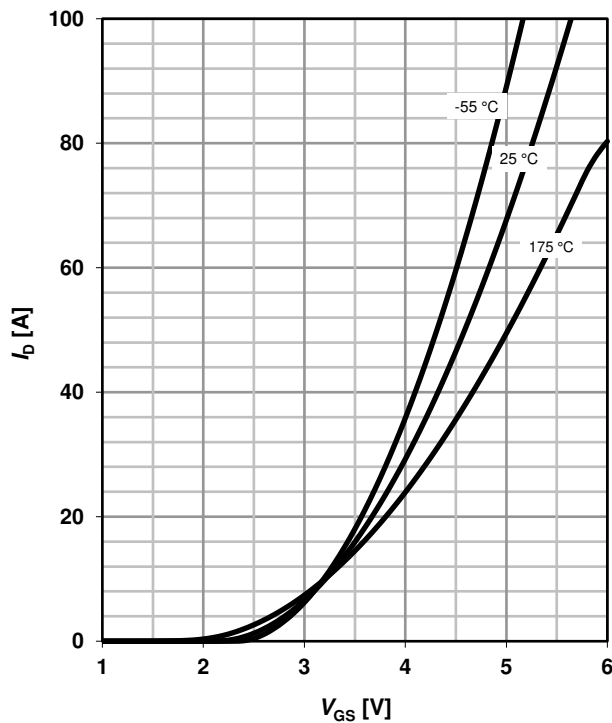
$$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$$

 parameter: V_{GS}

6 Typ. drain-source on-state resistance

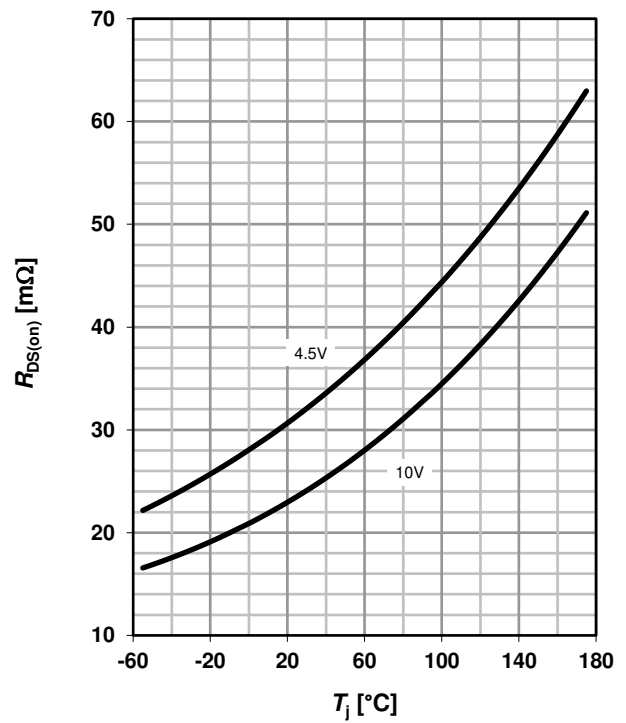
$$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$$

 parameter: V_{GS}

7 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} = 6\text{ V}$$

 parameter: T_j

8 Typ. drain-source on-state resistance

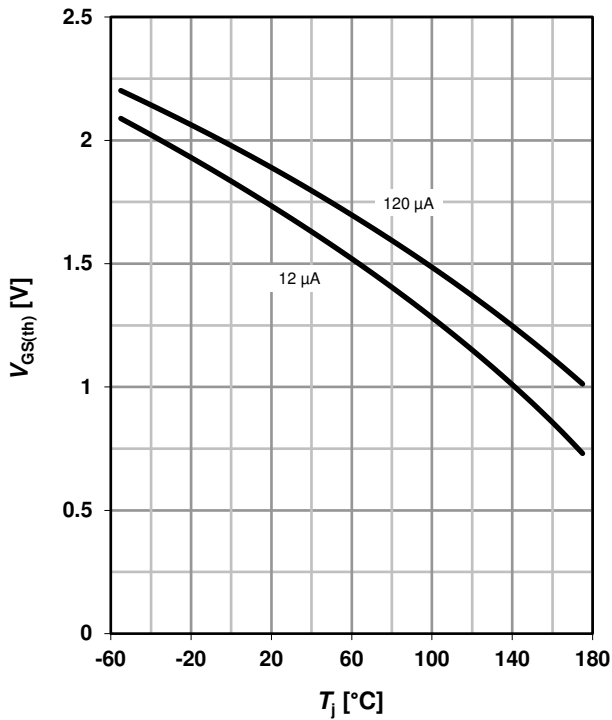
$$R_{DS(on)} = f(T_j); I_D = 12\text{ A}$$

 parameter: V_{GS}


9 Typ. gate threshold voltage

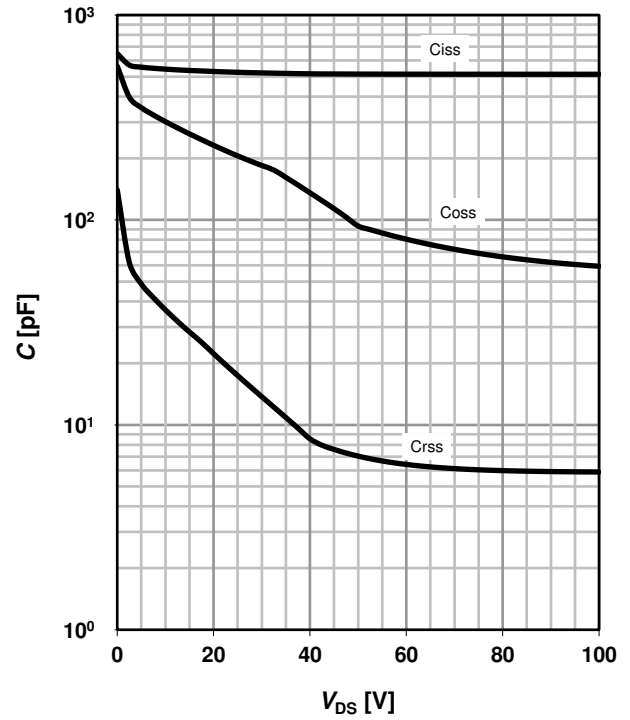
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter: I_D



10 Typ. capacitances

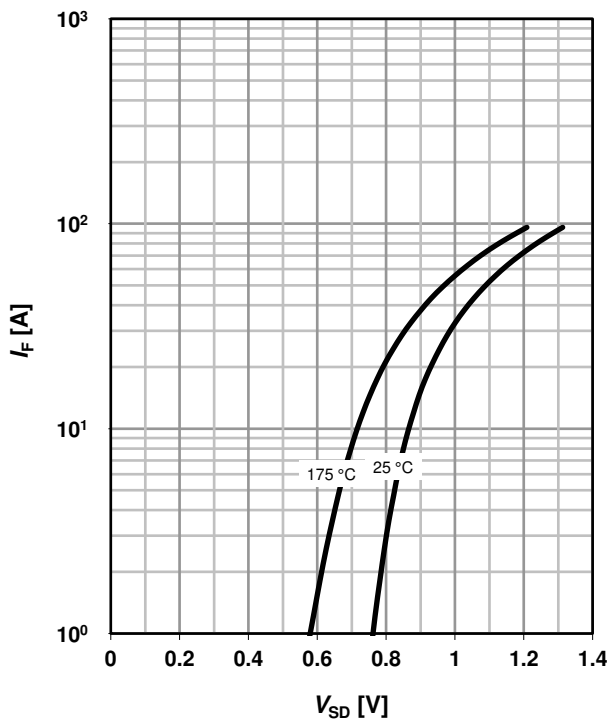
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



11 Typical forward diode characteristics

$I_F = f(V_{SD})$

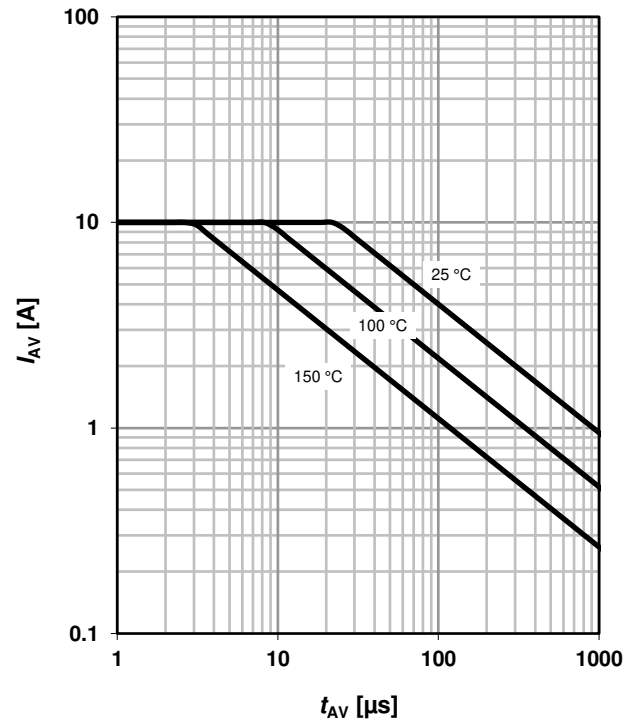
parameter: T_j



12 Typ. avalanche characteristics

$I_{AS} = f(t_{AV})$

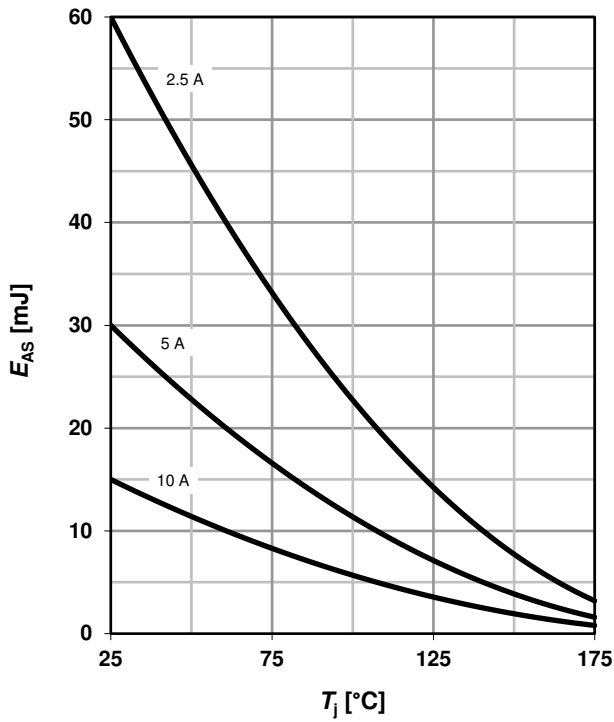
parameter: $T_{j(start)}$



13 Typical avalanche energy

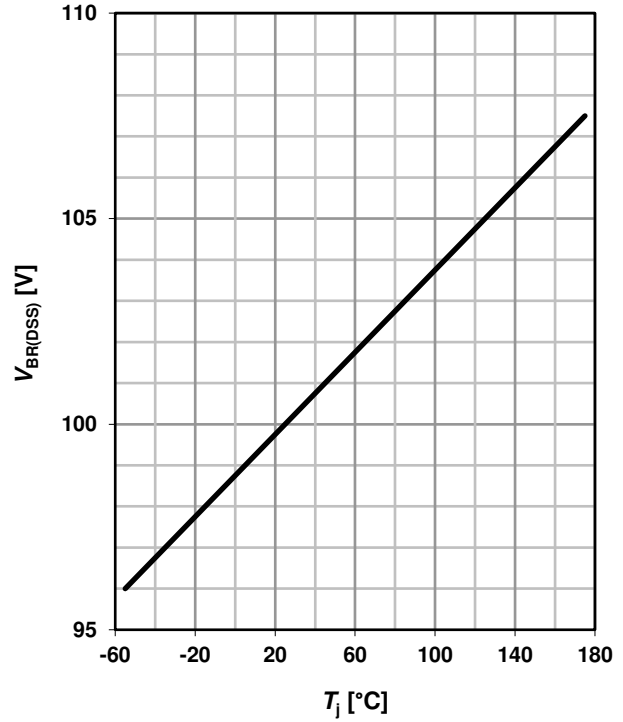
$$E_{AS} = f(T_j)$$

parameter: I_D



14 Drain-source breakdown voltage

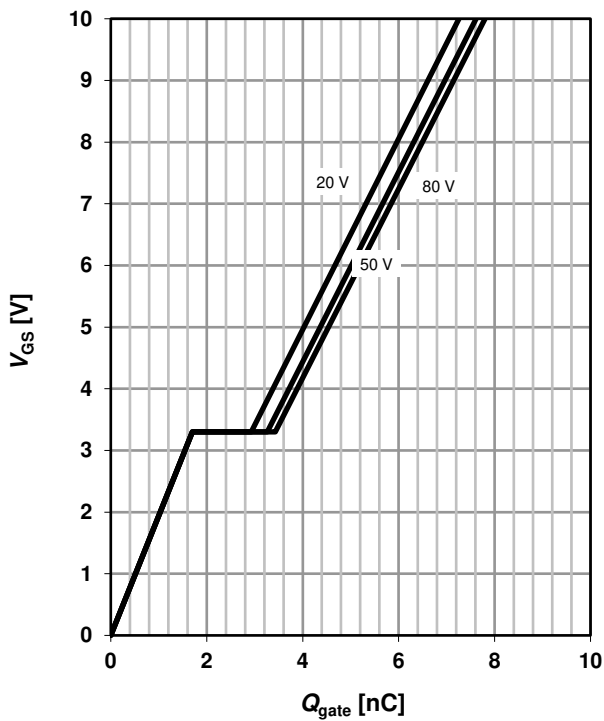
$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$



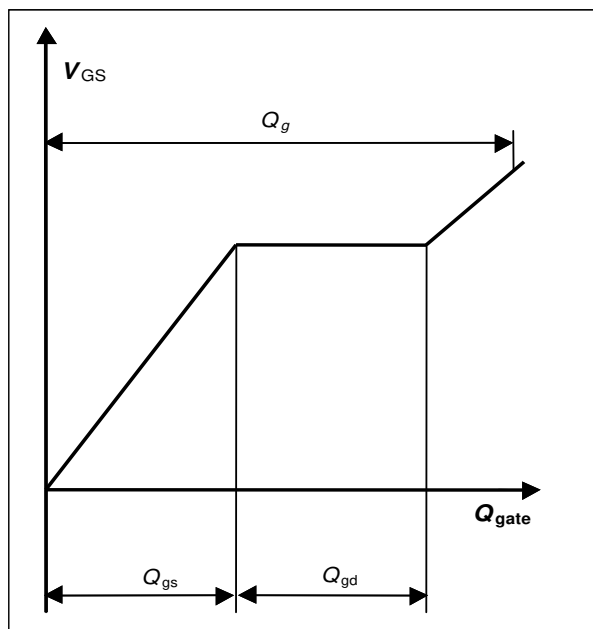
15 Typ. gate charge

$$V_{GS} = f(Q_{gate}); I_D = 12 \text{ A pulsed}$$

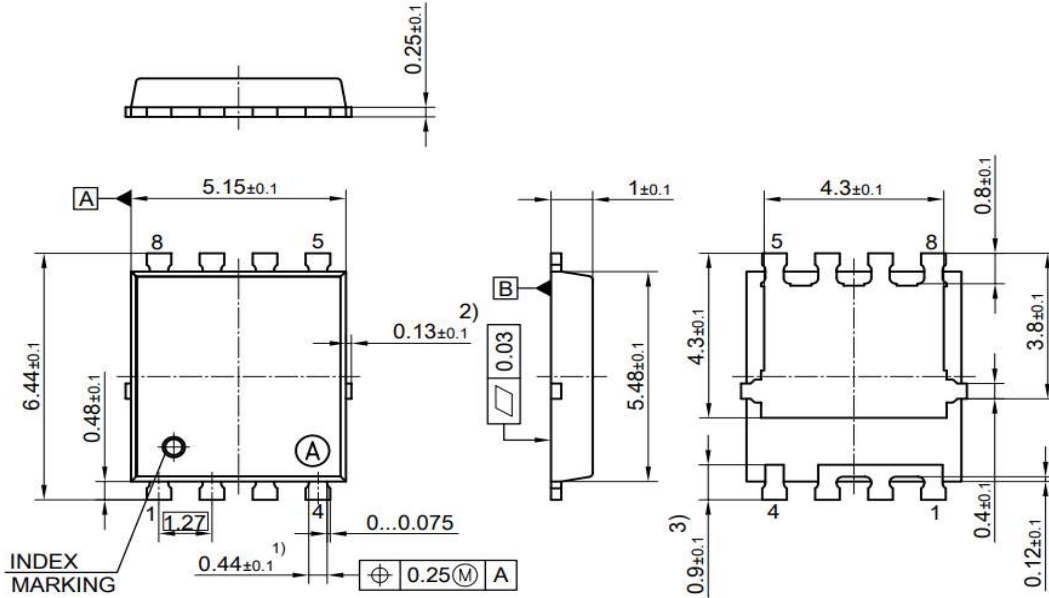
parameter: V_{DD}



16 Gate charge waveforms

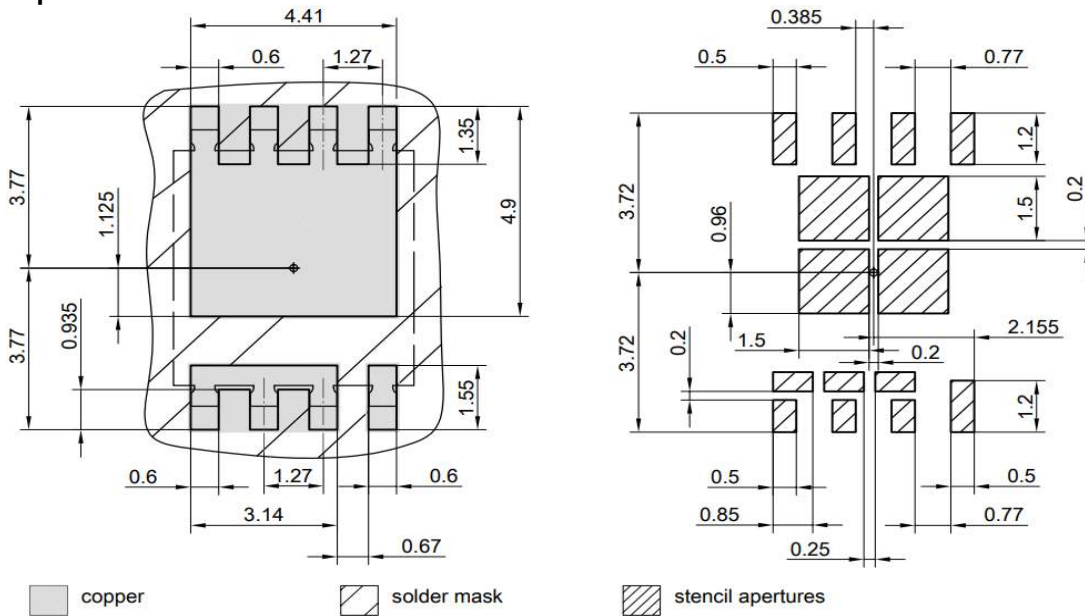


PG-TDSON-8: Outline



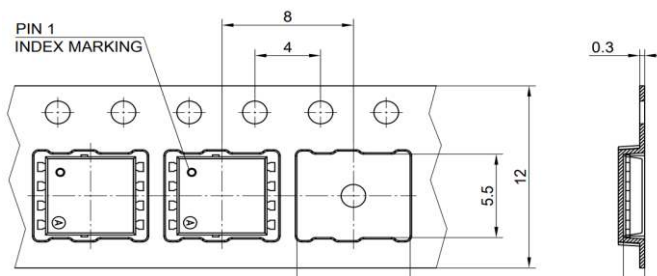
- 1) EXCLUDE MOLD FLASH
 - 2) REMOVAL ON MOLD GATE, INTRUSION 0.1MM AND PROTRUSION 0.1MM
 - 3) LEAD LENGTH UP TO ANTI FLASH LINE
 - 4) ALL METAL SURFACE ARE PLATED, EXCEPT AREA OF CUT
- ALL DIMENSIONS ARE IN UNITS MM
 THE DRAWING IS IN COMPLIANCE WITH ISO 128 & PROJECTION METHOD 1 []

Footprint



Dimensions in mm

Packaging



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If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

Revision History

Version	Date	Changes
Revision 1.0	23.07.2019	Final Data Sheet